

OK
see also
8/18/01

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-6. **(Cancelled)**

7. **(Currently Amended)** A silicon single crystal wafer which is a wafer prepared by means of a Czochralski method, the silicon single crystal wafer comprising at least one portion formed of an OSF ring portion in a peripheral region of the silicon single crystal wafer in contact with a boat on which the silicon single crystal wafer is placed for heat treatment.

8. **(Previously Presented)** A silicon single crystal wafer according to claim 7, wherein the OSF ring region is an annular region with a width of 10 mm or less from a periphery of the silicon single crystal wafer.

9. **(Previously Presented)** A silicon single crystal wafer according to claim 7, wherein a nitrogen concentration in the silicon single crystal wafer is in the range of 1×10^{10} to $5 \times 10^{15}/\text{cm}^3$.

10. **(Previously Presented)** A silicon single crystal wafer according to claim 8, wherein a nitrogen concentration in the silicon single crystal wafer is in the range of 1×10^{10} to $5 \times 10^{15}/\text{cm}^3$.

11. **(Currently Amended)** A manufacturing process for a silicon single crystal wafer comprising the steps of:

growing a silicon single crystal rod by means of a Czochralski method in a condition that an OSF ring region is formed in a peripheral region of the silicon single crystal rod; and

slicing the grown silicon ~~signal~~ single crystal rod into silicon single crystal wafers,